



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Ralph H. Johnson et al.

Examiner: unknown

Serial No.: 10/617,290

Group Art Unit: unknown

Filed: July 10, 2003

For: VERSATILE METHOD AND SYSTEM FOR SINGLE MODE VCSELS

Docket No.: H26341-D1 (1139.1124103)

INFORMATION DISCLOSURE STATEMENT (37 C.F.R. §1.97(b))

Assistant Commissioner for Patents

PO Box 1450

Alexandria, VA 22313-1450

CERTIFICATE UNDER 37 C.F.R. 1.8: I hereby certify that this correspondence is being deposited with the United States Postal Service on the date shown below with sufficient postage as first class mail in an envelope addressed to the: Commissioner for Patents, PO Box 1450, Alexandria, VA 22313-1450, on this 15th day of September, 2003.
By: Brian N. Tufte

Dear Sir/Madame:

With regard to the above-identified application, the items of information listed on the enclosed Form 1449 are brought to the attention of the Examiner.

This statement should be considered because it is submitted before the mailing date of a first Office Action on-the-merits. Accordingly, no fee is due for consideration of the items listed on the enclosed Form 1449.

No representation is intended to be made hereby that any of the cited references establishes, by itself or in combination with other information, a prima facie case of unpatentability of any claim of the present case.

Consideration of the items listed is respectfully requested. Pursuant to the provisions of M.P.E.P. 609, it is requested the Examiner return a copy of the attached

Form 1449, marked as being considered and initialed by the Examiner, to the undersigned with the next official communication.

Attached is a copy of the 1449 filed in parent application serial no. 09/724,820.

This application relies, under 35 U.S.C. § 120, on the earlier filing date of prior application Serial No. 09/724,820, filed on November 28, 2000. The references not provided but listed on PTO-Form 1449 were previously submitted in the above-referenced prior application and, therefore, are not required to be provided on this application under 37 CFR §1.98(d).

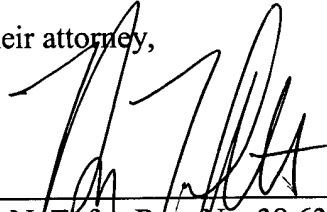
Also attached is a Form PTO 1449 citing additional references for consideration by the Examiner.

Respectfully submitted,

Ralph H. Johnson et al.

By their attorney,

Dated: September 15, 2003



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Examiner Initial	Document No.	Date	Name	Filing Date If Appropriate
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DU B	WO 02/17445 A1	02/28/2002	PCT	
DU C	WO 03/023457 A1	03/20/2003	PCT	

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER:

DATE CONSIDERED:

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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